

## P416B Datasheet, Equivalent, Cross Reference Search

Type Designator: P416B

Material of Transistor: Ge

Polarity: PNP

Maximum Collector Power Dissipation ( $P_c$ ): 0.1 W

Maximum Collector-Base Voltage  $|V_{cb}|$ : 12 V

Maximum Collector-Emitter Voltage  $|V_{ce}|$ : 12 V

Maximum Emitter-Base Voltage  $|V_{eb}|$ : 3 V

Maximum Collector Current  $|I_c \text{ max}|$ : 0.025 A

Max. Operating Junction Temperature ( $T_j$ ): 75 °C

Transition Frequency ( $f_t$ ): 80 MHz

Collector Capacitance ( $C_c$ ): 8 pF

Forward Current Transfer Ratio (hFE), MIN: 90

Noise Figure, dB: -